

10 days - workshop

(VLSI)

→ silicon valid chip

⇒ designing a processor.

100MHz - 180MHz

RISC - V

⇒ we are designing a processor.

Compiler in one language (Application is written in the C language)

→ GCC → Application

we will take a code and run in

01 step = ① take a code and run in the GCC

step = 2 some code in one spec (C model)

if  $00 = 01$  ✓

After meeting

step = 2 we will write a soft copy of one hotel word using RTL (Verilog)

02 have to check  $01 == 02$

soc design

Processor

should be synthesized  
to gates

GPN (Synth P)

peripherals (ips) APIC

synthesis

macro (memory)

(synth RTL)

pre defined use me instance

analog IP

(oscillators)

ADC, Phase lock loop  
(PLL)  
clock multiplier.

03

step = 4

SOC integration  
check  $03 == 02$

need not be  
synthesizable, we will  
explore by myself

next step ⇒ APR (RTL2GDS)

(only those box not on one  
whole chip)

GDSII → fab (step out)

04

Neophony (like the  
(USS, rats)  
We will write the  
Code in C for this application  
I generate output

$$O_1 = O_2 = O_3 = O_4$$

O → output

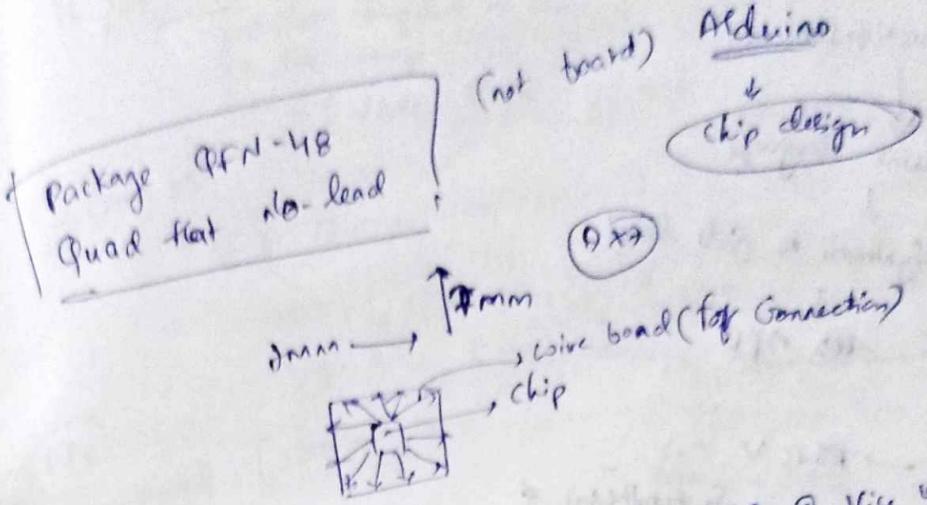
100MHz → 130MHz

application

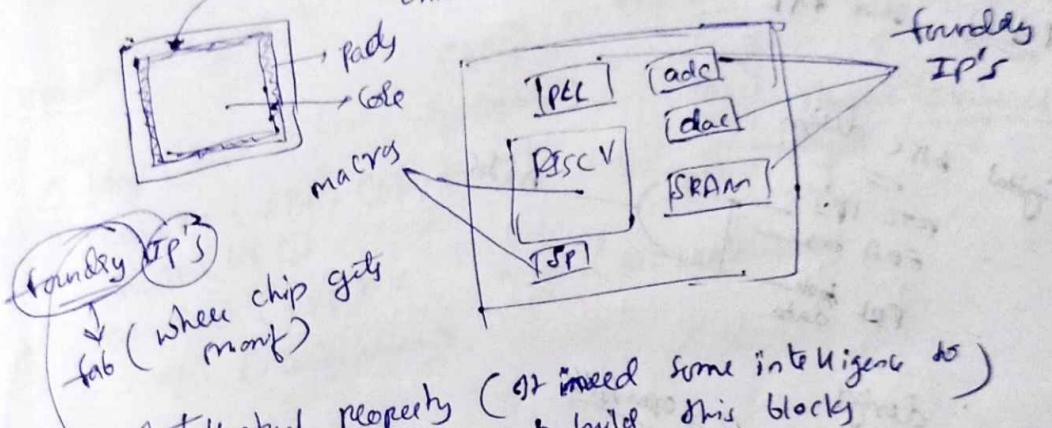
→   
Pcb board  
TV panel

1. 400  
1113 faults  
98 Pkg

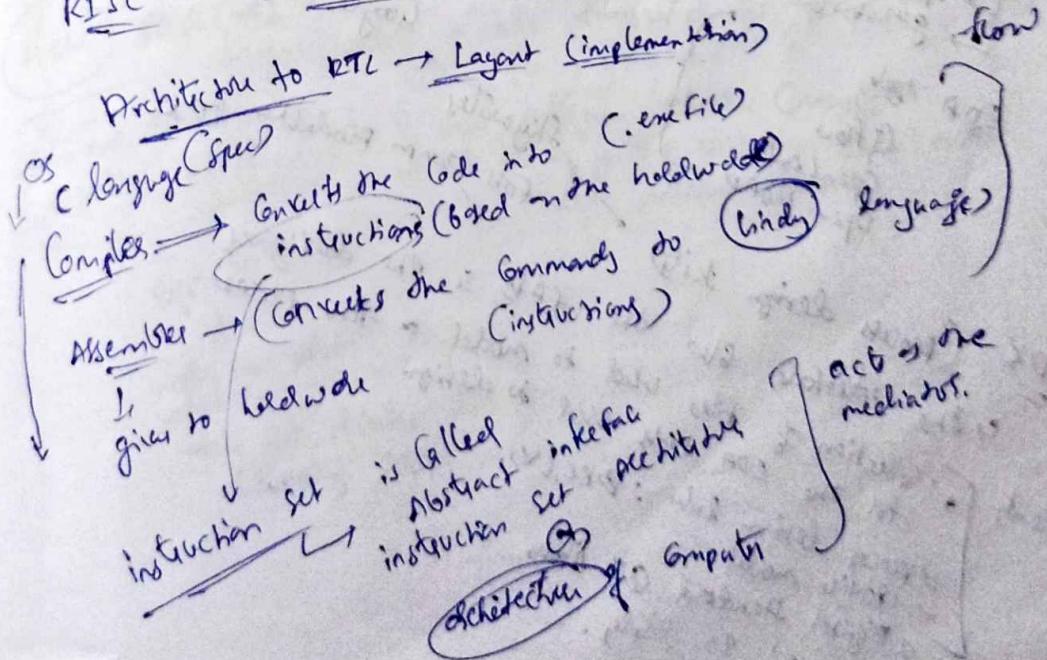
2. Special note  
use not total



Pads → sends signals from inside to outside (as via ICES) chip to outside (package or world) outside to chip outside the chip



## RISC-V (Instruction set architecture (ISA))



instruction set

↓  
hardware language

J  
Synthesis to gate level.

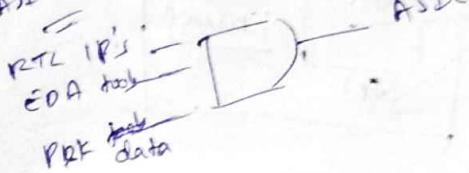
↓  
→ APP

Pdt → ① → RISC V

Pdt → ② → RTL & synthesis of  
RISC → hard CPU core - picard 82

Pdt → ③ → APP

Digital ASIC design



RTL design

- ↳ libde2res.org
- ↳ openres.org
- ↳ github.com

EDA tool

- ↳ flow
- ↳ OpenLANT
- ↳ OpenROAD

→ open source

Google

Skywater +  
TSMC Bonn Production PDK

PDK (Process Design Kit)

↳ The interface file is the fab in the designer

↳ Collection of files used to model a fab process

for the EDA tools used to design

↳ Process design rule : DRC, LVS, ...

↳ Device model

↳ Digital Standard Cell Library

↳ To library . -

Content

is 130nm fast  
not complicated to now  
very cheap  
G.I. Shole value

Yes (may be)

Ug of 130nm

intel : PU EE @ 3.46GHz (quion)

single cycle RV32i design (300-400MHz)

APP  
flow explained  
from synthesis to sign off  
(exception helpful)

openlane → good for flow configuration  
(CLC)

Yosys (RTL to GLN) (Synthesis)

openSTA (STA) (openROAD)

fault (DFT)

openRoad (APP)

magic (Verification)

openlane (like a container)

(1.5-5,000 - 200,000)  
Area (million)

6 layers

sky130nm (area m5 thinning  
mermo aluminum  
aluminum)

(abc) → ~~negative~~ strategies  
→ gadgets

netgen (RC extraction)

New step (\*)

fake ant. diodes  
injection script

↓ before to ranking

↓ after the detail ranking

fake ant. diodes  
swapping script

adds a fake antenna diode next to every  
cell after placement  
↓ len Antenna checker (magic)  
→ if we are getting violation then add  
the real antenna diode.

PLK5 → Skylane 13nm  
Skywater

(HDL, lib, ref, tech ref, ref)

• LSSD → timing

LSSD → tool related constraint

Micro 32a → design

BRD → RTL (V)

SNC

→ Config. tcl

clock

period  $\leq$  CTC

Command  
→ Getting all the Commands.

day ① → done synthesis, Count  
find the DFF ratio (1.)

$$DFRP \Rightarrow \frac{ff}{Total Cells} \times 100$$

test ①

$$\begin{aligned} \text{no of Cells} &= 14826 \quad \therefore \frac{1613}{14826} \times 100 \\ DF &= 1613 \quad \therefore \quad = 10.8\% \end{aligned}$$

Day 2 defining the die & die

→ ~~Defining width & height of die~~

⇒ die & die.

Utilization factor =  $\frac{\text{Area occupied by die}}{\text{Total Area of die}}$

ideal utilization = 100%.

practical utilization = 80-85%.

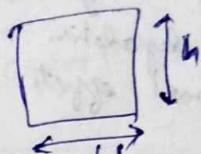
good to start at 1 60-70%.

100% = 1 = Utilization factor

Aspect ratio =  $h/w$

h = height  
w = width

( $\Rightarrow$ ) square  
( $\Rightarrow$ ) rectangle.



② define location of populated cells. → Macro, & P's

Partitioning → This is need revised

⇒ macro guidelines (explained)

→ decoupling Capacitance

⇒ we have to subdivide the decoupling capacitance around the macro.

→ floorplan ((die Configuration))

Readme file

⇒ we will have some validity in this

→ powerplan

↳ we will place the main wire for one connection of the power & ground pins of all the cells.

→ Need for characterization of libraries

Cell design flow

(input)  $\Rightarrow$  process design kit (PDK):

New formulae & User-defined Specs

Dec & V<sub>t</sub> rules, Spike models

Height-cell supply voltage, m-layers  
Pin locations etc.

Spike models contains

I-V characteristic

Threshold Voltage ( $V_{th}$ )

Mobility degradation

Short channel effects

Short short channel modulation.

Typical spike model looks like

Model runs other level =  $\Theta$

$$+ V_{th0} = 0.45 \quad n_0 = 0.05 \quad t_{on} = 1.4 \times 10^{-9}$$

$$+ \gamma_{ds0} = 150 \quad \eta_{ta0} = 0.01 \quad K_1 = 0.5 \quad K_2 = 0.02$$

Design story

$\Rightarrow$  Circuit design, layout design.

We will implement  
the things in the  
layout.

Characterization

Design one circuit with  
one memory.

H/W to run

L/W to run

Outputs

Circuit description language (Circuit design)

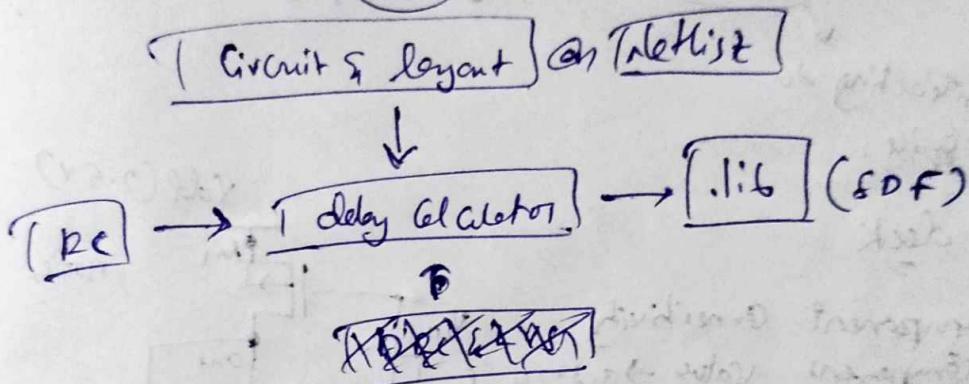
GDS II, Lef, RC extraction (Layout design)

Timing, noise, power diss., function.

- Mod diagram → Euler path & drew stick diagram
- & after we will design the layouts  
in the tool using all the DRC & LVS  
rules.

→ After characterization. (Guna software)

Let's see the process of generating the timing & function of the design in the standard formats called .lib.



⇒ for learning one flop/plan, we use

ctrl-flop/plan

→ we will set all the required switches before learning the flop/plan.

→ Shift + W (to go to last line of the script)

→ S + V → align layout to center

→ Z → Zoom in

Shift + Z → Zoom out

→ Registration

Day - 3

=  $\Rightarrow$  To place circuit

$\Rightarrow$  Spike deck Creation for component

$\rightarrow$  extract

$\hookrightarrow$  for extracting the design

$\rightarrow$  extract

ext2spike cthreshold strength

extracting do

spike.

Spike deck

$\hookrightarrow$  Component Connectivity

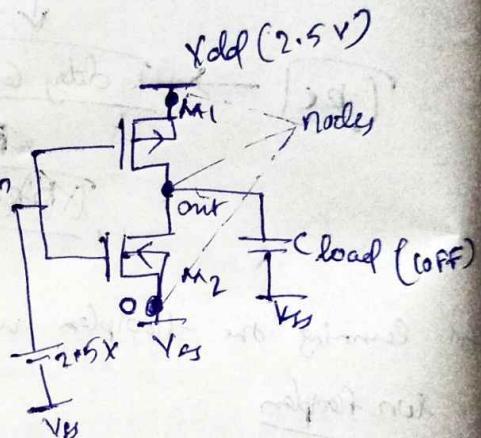
$\hookrightarrow$  Component value  $\Rightarrow 0.375\mu$

$\rightarrow$  identify "nodes"

$\rightarrow$  name "nodes"

$$\frac{0.25}{W} = \frac{0.375\mu}{L}$$

both P&N



$\star \star$  Model description  $\star \star$

$\star \star$  Netlist description  $\star \star$

M1 out in Vdd Vdd PMOS  $W=0.375\mu$   $L=0.25\mu$

M2 out in 0 0 NMOS  $W=0.375\mu$   $L=0.25\mu$

Load out 0 10f

Vdd Vdd 0 2.5

Vin in 0 2.5

$\star \star$  Simulation Commands  $\star \star$

.op

.dc Vin 0 2.5 0.05

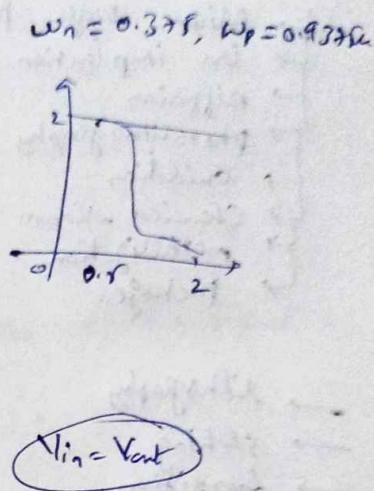
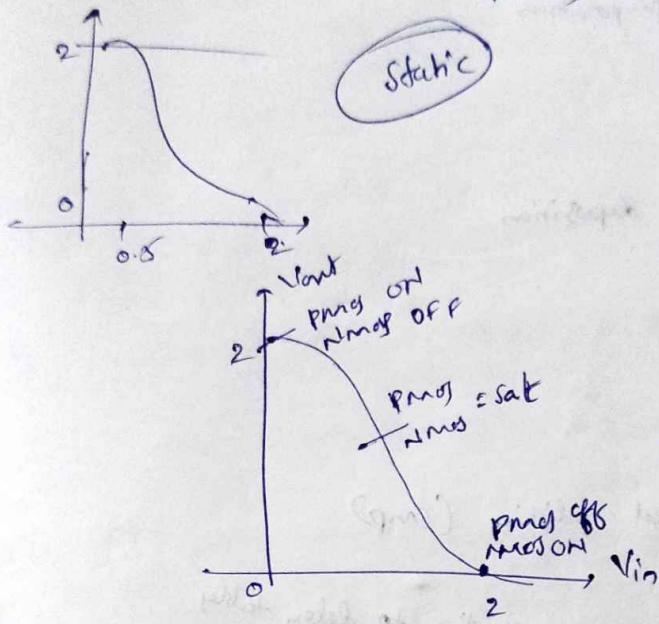
$\star \star \star$  include "tmc\_025um\_model.mod"  $\star \star \star$

.lib "tmc\_025um\_model.mod" Cmos-models

.end

Epile Wallförm:  $\omega_n = \omega_p = 0.375\text{ rad/s}$ ,  $L_n, \rho = 0.2\text{ m}$  drehig

$$(L_n/L_n = \omega_p/\omega_p = 1.5)$$



→ 16 - mask Comes plaus

finden Length  
split

list → for Creating the list  
split → for splits a string into a list  
join → joins list element into a string  
concat → concatenates list

→ length  
→ finden (returns a element at a given index)

→ length  
→ finden

→ replace

→ set (modifies a specific list element)

→ search

→ sort (sorts a list) (including order, A-Z)

→ append (appends an element to a list  
(variable))

→ for each → iterates over list items

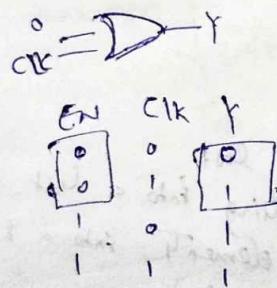
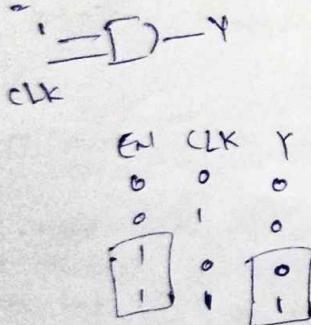
## Fabrication steps

- silicon wafer preparation
- ion implantation
- diffusion
- photolithography
- oxidation
- Chemical-vapor deposition
- metallization
- package.

- lithography
- etching
- deposition
- chemical mechanical polishing (cmp)
- em

Introduction to delay tables

Day = 4



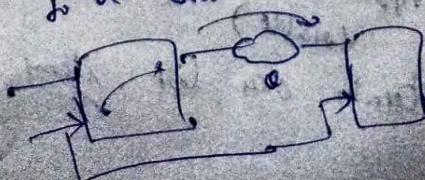
⇒ delay tables are the representation of delay of all the gates.

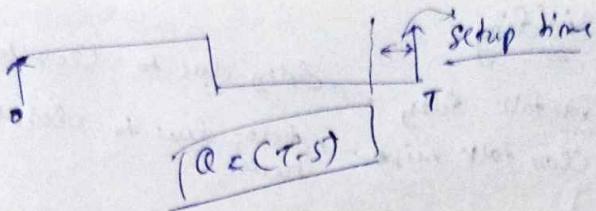
⇒ delay depends on input slew output load

Slow output of one gate is equal to the slow input of next gate.

Setup time

⇒ The time interval between the active clock edge and the data need to be stable.





Uncertainty

$$U_C = \text{jitter} + \text{skew} + \text{margin}$$

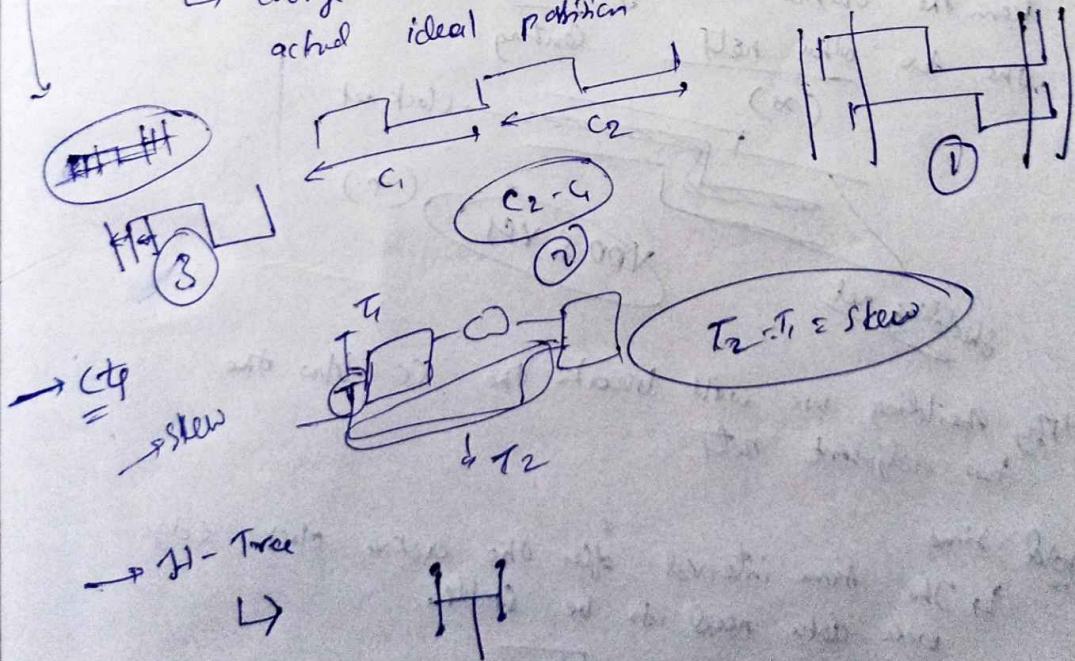
jitter  $\rightarrow$  undesired deviation occurred in the clock signal

period jitter  $\rightarrow$  cycle-to-cycle jitter  $\rightarrow$  absolute jitter

① Absolute jitter  
 $\rightarrow$  change in the clock position from its ideal position

cycle-to-cycle jitter  
 $\rightarrow$  difference of two cycles clock cycles

③ Period jitter (used in STA)  
 $\rightarrow$  change in the transition of the clock from its actual ideal position

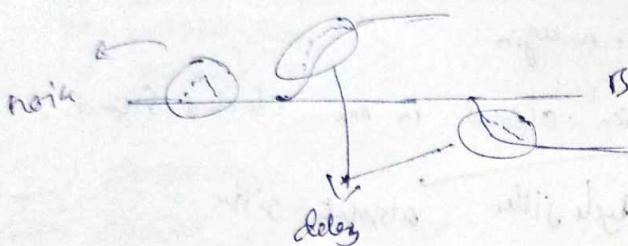


## Clock net shielding

Cross talk → cross talk delay → delay due to cross talk  
 Cross talk noise → delay due to cross talk noise  
 (Signal integrity)

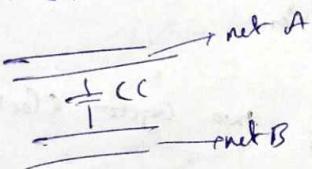
A

A = aggressor

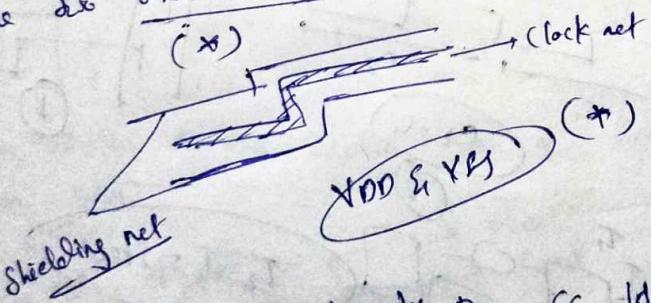


B = victim

→ Crosstalk occurred due to the Coupling Capacitance b/w the two adjacent nets.



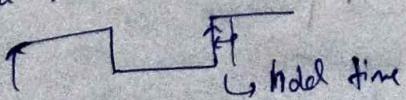
→ Clock net shielding means protecting the clock net from the outside sides by placing the clock net in the routing of the other nets.



→ By shielding we will break the CC b/w the two adjacent nets

Hold time

↳ The time interval after the active clock edge well data need to be stable.



Day-5

27

25-11-14-0-3

MUM  
gat

ENS - 3854.15

WNS - 3666.2

27-11-09-0-2

New strategy haven't set

ENS = -266.63

WNS = -2.95

here set

## Routing

- Global route (imaging)
- track assignment
- detailed route
- search & repair.

is the process of creating metal wire to all the signal & clock pins.